

isc Silicon NPN Power Transistor

BUV48AFI

DESCRIPTION

- High Voltage Capability
- High Current Capability
- Fast Switching Speed

APPLICATIONS

Designed for high-voltage,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switchmode applications such as:

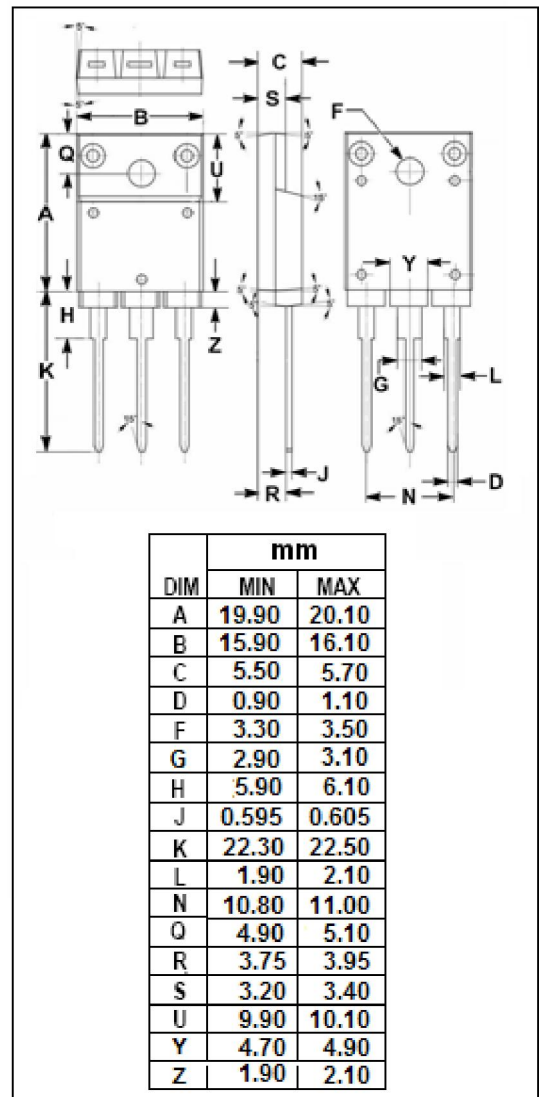
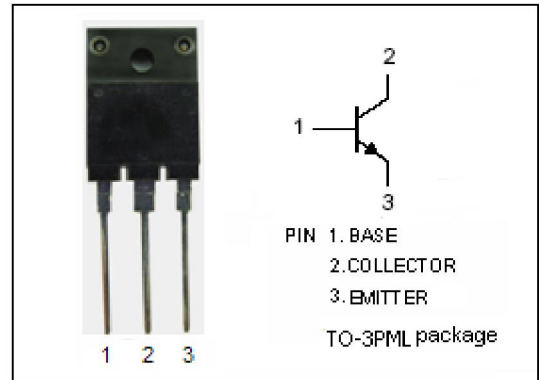
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)	1000	V
V _{CER}	Collector-Emitter Voltage (R _{BE} = 10 Ω)	1000	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	15	A
I _{CM}	Collector Current-Peak	30	A
I _B	Base Current-Continuous	4	A
I _{BM}	Base Current-peak	20	A
P _C	Collector Power Dissipation @T _C =25°C	55	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	2.2	°C/W



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2\text{A}$; $I_B=0$; $L=25\text{mH}$	450		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\text{mA}$; $I_C=0$	7		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}$; $I_B=1.6\text{A}$		1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=12\text{A}$; $I_B=2.4\text{A}$		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8\text{A}$; $I_B=1.6\text{A}$		1.6	V
I_{CER}	Collector Cutoff Current	$V_{CE}=\text{rated } V_{CER}$; $R_{BE}=10\Omega$ $V_{CE}=\text{rated } V_{CER}$; $R_{BE}=10\Omega$; $T_C=125^{\circ}\text{C}$		0.5 4.0	mA
I_{CES}	Collector Cutoff Current	$V_{CE}=\text{rated } V_{CES}$; $V_{BE(off)}=1.5\text{V}$ $V_{CE}=\text{rated } V_{CES}$; $V_{BE(off)}=1.5\text{V}$; $T_C=125^{\circ}\text{C}$		0.2 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}$; $I_C=0$		1.0	mA
h_{FE}	DC Current Gain	$I_C=10\text{A}$; $V_{CE}=5\text{V}$	8		

Switching times Resistive Load

t_{on}	Turn-on Time	$I_C=8\text{A}$; $I_{B1}=1.6\text{A}$; $V_{CC}=150\text{V}$		1.0	μs
t_s	Storage Time	$I_C=8\text{A}$; $I_{B1}=-I_{B2}=1.6\text{A}$; $V_{CC}=150\text{V}$		3.0	μs
t_f	Fall Time			0.8	μs